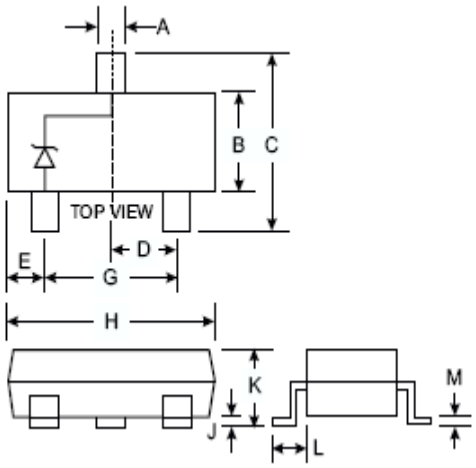
JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-23 Plastic-Encapsulate DIODE

BZX84C2V4-BZX84C39

Features

- **Planar Die Constrruction**
- **350mW Power Dissipation**
- **Zener Volages from 2.4V-39V**
- **Ldeally Suited for Automated Assembly Processes**



SOT-23		
Dim	Min	Max
A	0.37	0.51
B	1.19	1.40
C	2.10	2.50
D	0.89	1.05
E	0.45	0.61
G	1.78	2.05
H	2.65	3.05
J	0.013	0.15
K	0.89	1.10
L	0.45	0.61
M	0.076	0.178
All Dimensions in mm		

MAKING see table on page 2 the first code

Maximum Ratings @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Forward Voltage @ I_F = 10mA	V_F	0.9	V
Power Dissipation (Note 1)	P_d	350	mW
Thermal Resistance, Junction to Ambient Air (Note 1)	$R_{\theta JA}$	357	K/W
Operating and Storage Temperature Range	T_j, T_{STG}	-65 to +150	°C

Notes: 1. Valid provided that device terminals are kept at ambient temperature.
2. Tested with pulses, 300μs pulse width, period = 5ms.
3. f = 1KHz.

Electrical Characteristics @ T_A= 25° C unless otherwise specified

Type Number	Type Code	ZenerVoltage Range (Note 2)				Maximum Zener Impedance (Note 3)			Maximum Reverse Current		Temperature Coefficent of Zener voltage @ I_{ZT}=5Ma	
		V_Z@I_{ZT}			I_{ZT}	Z_{ZT}@I_{ZT}	Z_{ZK}@I_{ZK}	I_{ZK}	I_R	V_R	mV/° C	
		Nom(V)	Min(V)	Max(V)	(mA)	(Ω)		(mA)	(uA)	(V)	Min	Max
BZX84C2V4	Z11	2.4	2.20	2.60	5	100	600	1.0	50	1.0	-3.5	0
BZX84C2V7	Z12	2.7	2.5	2.9	5	100	600	1.0	20	1.0	-3.5	0
BZX84C3V0	Z13	3.0	2.8	3.2	5	95	600	1.0	10	1.0	-3.5	0
BZX84C3V3	Z14	3.3	3.1	3.5	5	95	600	1.0	5	1.0	-3.5	0
BZX84C3V6	Z15	3.6	3.4	3.8	5	90	600	1.0	5	1.0	-3.5	0
BZX84C3V9	Z16	3.9	3.7	4.1	5	90	600	1.0	3	1.0	-3.5	0
BZX84C4V3	Z17	4.3	4.0	4.6	5	90	600	1.0	3	1.0	-3.5	0
BZX84C4V7	Z1	4.7	4.4	5.0	5	80	500	1.0	3	2.0	-3.5	0.2
BZX84C5V1	Z2	5.1	4.8	5.4	5	60	480	1.0	2	2.0	-2.7	1.2
BZX84C5V6	Z3	5.6	5.2	6.0	5	40	400	1.0	1	2.0	-2.0	2.5
BZX84C6V2	Z4	6.2	5.8	6.6	5	10	150	1.0	3	4.0	0.4	3.7
BZX84C6V8	Z5	6.8	6.4	7.2	5	15	80	1.0	2	4.0	1.2	4.5
BZX84C7V5	Z6	7.5	7.0	7.9	5	15	80	1.0	1	5.0	2.5	5.3
BZX84C8V2	Z7	8.2	7.7	8.7	5	15	80	1.0	0.7	5.0	3.2	6.2
BZX84C9V1	Z8	9.1	8.5	9.6	5	15	100	1.0	0.5	6.0	3.8	7.0
BZX84C10	Z9	10	9.4	10.6	5	20	150	1.0	0.2	7.0	4.5	8.0
BZX84C11	Y1	11	10.4	11.6	5	20	150	1.0	0.1	8.0	5.4	9.0
BZX84C12	Y2	12	11.4	12.7	5	25	150	1.0	0.1	8.0	6.0	10.0
BZX84C13	Y3	13	12.4	14.1	5	30	170	1.0	0.1	8.0	7.0	11.0
BZX84C15	Y4	15	13.8	15.6	5	30	200	1.0	0.1	10.5	9.2	13.0
BZX84C16	Y5	16	15.3	17.1	5	40	200	1.0	0.1	11.2	10.4	14.0
BZX84C18	Y6	18	16.8	19.1	5	45	225	1.0	0.1	12.6	12.4	16.0
BZX84C20	Y7	20	18.8	21.2	5	55	225	1.0	0.1	14.0	14.4	18.0
BZX84C22	Y8	22	20.8	23.3	5	55	250	1.0	0.1	15.4	16.4	20.0
BZX84C24	Y9	24	22.8	25.6	5	70	250	1.0	0.1	16.8	18.4	22.0
BZX84C27	Y10	27	25.1	28.9	2	80	300	0.5	0.1	18.9	21.4	25.3
BZX84C30	Y11	30	28.0	32.0	2	80	300	0.5	0.1	21.0	24.4	29.4
BZX84C33	Y12	33	31.0	35.0	2	80	325	0.5	0.1	23.1	27.4	33.4
BZX84C36	Y13	36	34.0	38.0	2	90	350	0.5	0.1	25.2	30.4	37.4
BZX84C39	Y14	39	37.0	41.0	2	130	350	0.5	0.1	27.3	33.4	41.2

Notes: 1. Valid provided that device terminals are kept at ambient temperature.

2. Tested with pulses, period=5ms,pulse width =300us.

3.f = 1KH_Z